

4 ~~22~~ 22. (Amended) A method of forming a film on a substrate comprising the steps of:

placing a substrate in a reaction chamber;  
introducing a reactive gas comprising at least TEOS;  
supplying a photo energy to said reactive gas to excite said gas;  
depositing a first film on said substrate;  
stopping supplying said photo energy;  
supplying a [photo] electrical energy to said reactive gas to excite said gas; and  
depositing a second film on said first film.

63 ~~27~~ 10 ~~10~~ 25 5  
27. (Amended) The method of claim ~~25~~ wherein said leads are [about] 0.8 microns in height, [about] 0.6 microns in width, and a gap between each lead is [about] 0.9 microns.

63 ~~28~~ 11 ~~10~~ 25 5  
28. (Amended) The method of claim ~~25~~ further comprising the step of forming a [buffer] blocking layer between said substrate and the film formed on the substrate.

Please add new claim 31 as follows:

63 ~~31~~  
--31. A method for forming a film on a substrate comprising the steps of:  
forming a first layer comprising silicon oxide on a substrate by CVD using a first reactive gas comprising a carbon free silicon containing material; and